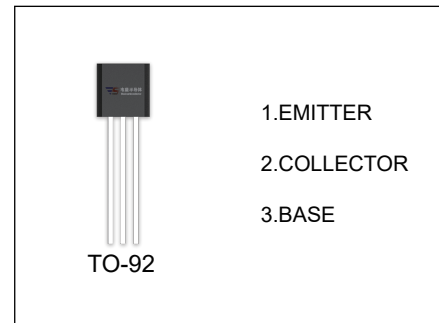


2SC2717 TRANSISTOR (NPN)

FEATURES

- High Gain: $G_{pe} = 33 \text{ dB}$ (Typ.) ($f = 45 \text{ MHz}$)
- Good Linearity of h_{FE} .



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SC2717	TO-92	Bulk	1000pcs/Bag
2SC2717-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	50	mA
P_C	Collector Power Dissipation	300	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55 ~ +150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	417	$^\circ\text{C/W}$

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE1}	$V_{CE}=12.5\text{V}, I_C=12.5\text{mA}$	90		320	
DC current gain	h_{FE2}	$V_{CE}=5\text{V}, I_C=50\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=15\text{mA}, I_B=1.5\text{mA}$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=15\text{mA}, I_B=1.5\text{mA}$			1.5	V
Transition frequency	f_T	$V_{CE}=12.5\text{V}, I_C=12.5\text{mA}$	300			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=30\text{MHz}$	0.8		2.0	pF
Collector-base time constant	$C_C^{.rb\dot{b}^t}$	$V_{CB}=10\text{V}, I_E=-1\text{mA}, f=30\text{MHz}$			25	ps
Power gain (fig.)	G _{pe}	$V_{CC}=12.5\text{V}, I_E=-12.5\text{mA}, f=45\text{MHz}$	28		36	dB